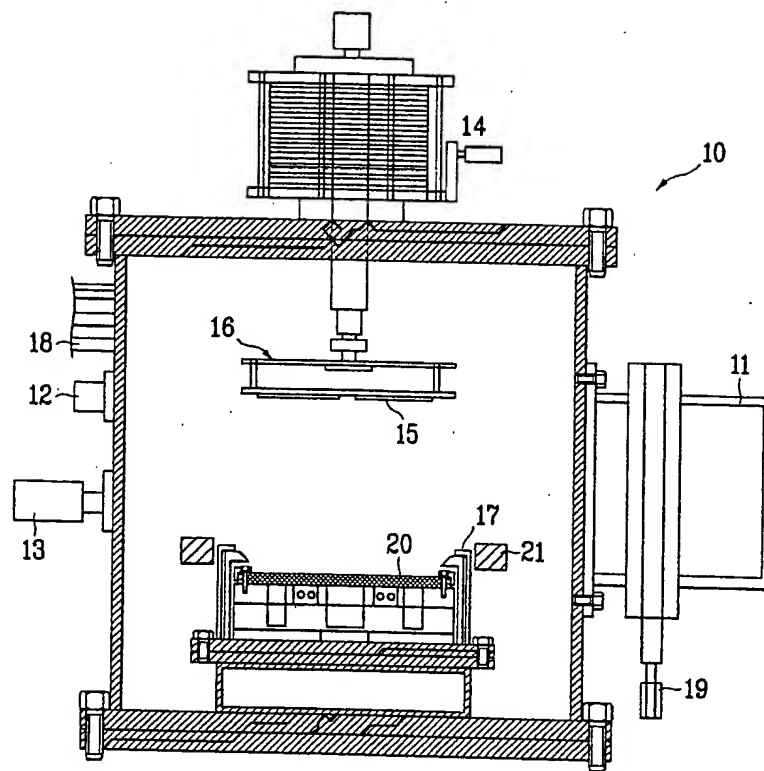
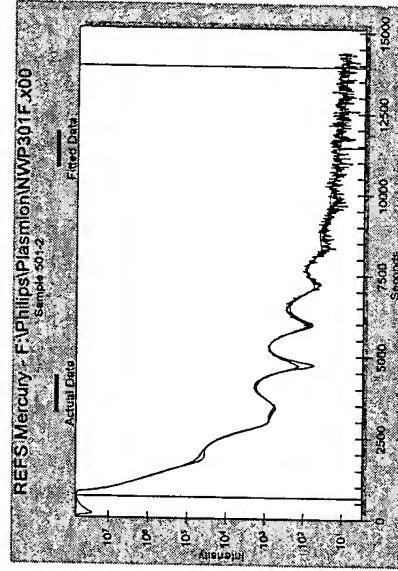


FIG.1

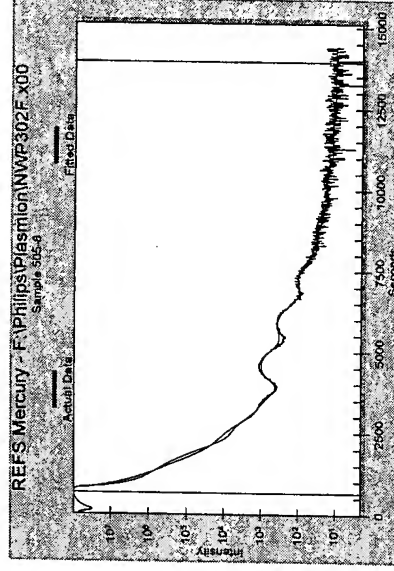




NSIB process



Conventional sputtering



Sample	Layer Description	Thickness (Å)	Relative Density (%)	Density (g/cm ³)
NSIB process	Si Layer	---	100 (fixed)	2.33
	SiO ₂	16.5±2.6	100 (fixed)	2.27
	Diamond Layer	108.4±1.3	86±2	3.03±0.02
	Diamond Layer	25.6±1.3	22±4	0.77±0.04
Conventional sputtering	Si Layer	---	100 (fixed)	2.33
	Diamond Layer	107.5±1.5	62±2	2.18±0.02
	Diamond Layer	24.2±0.8	33±2	1.16±0.02

FIG 2

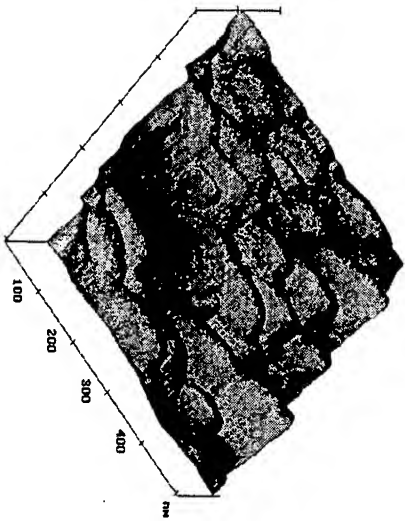


FIG 3A

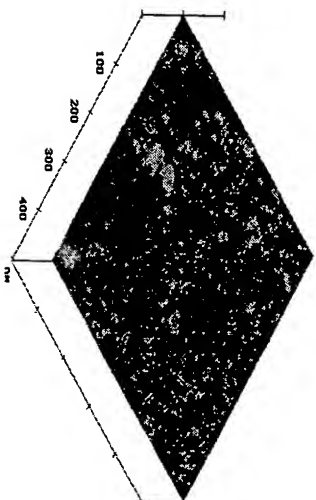


FIG 3B

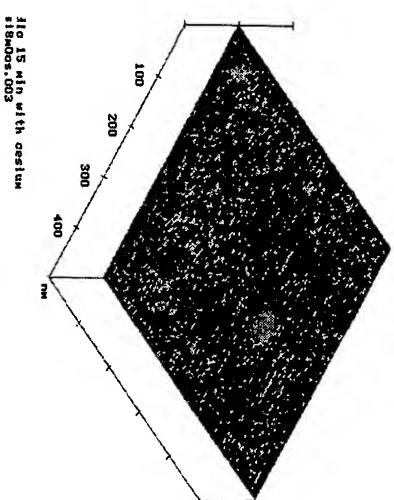


fig 15 with cesium
#15m00s.003

FIG 3C

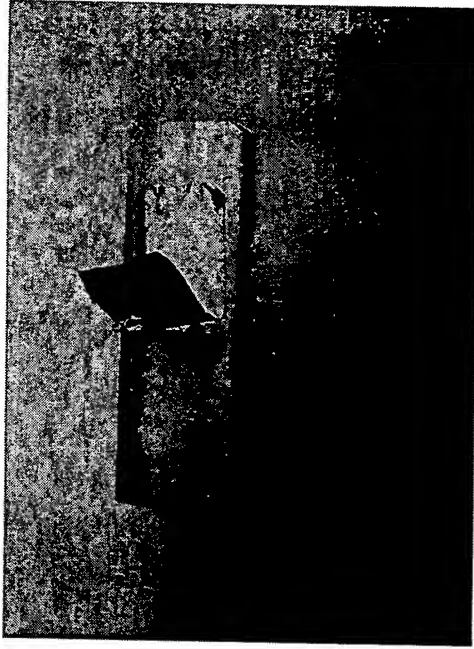


FIG 4A

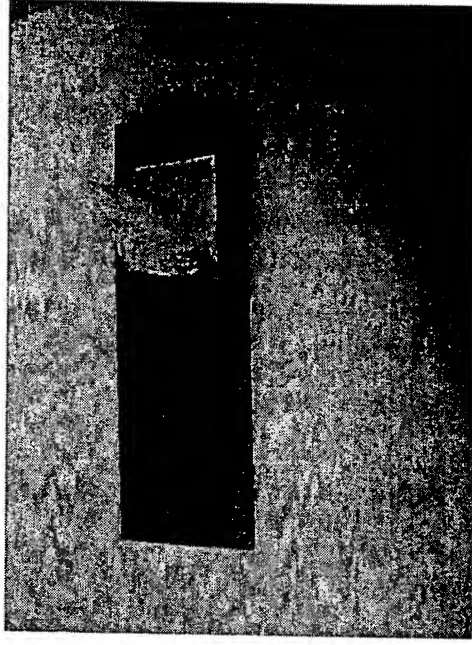


FIG 4B

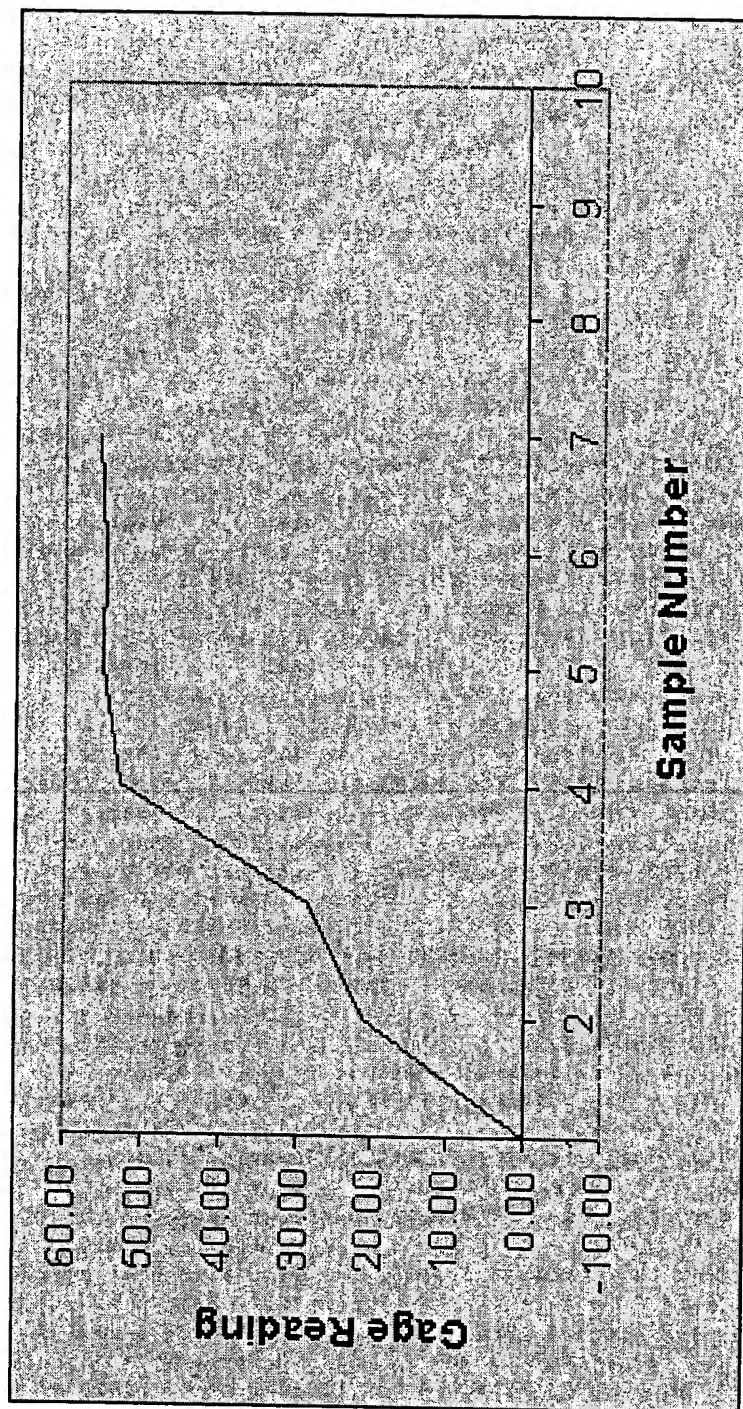


FIG 5

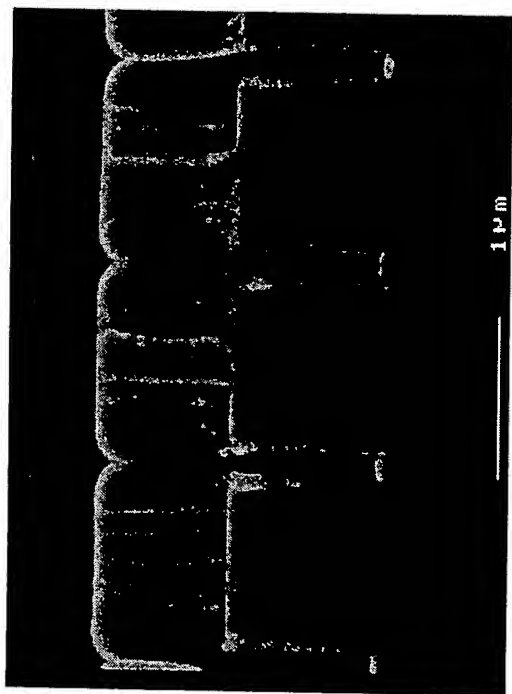


FIG 6A

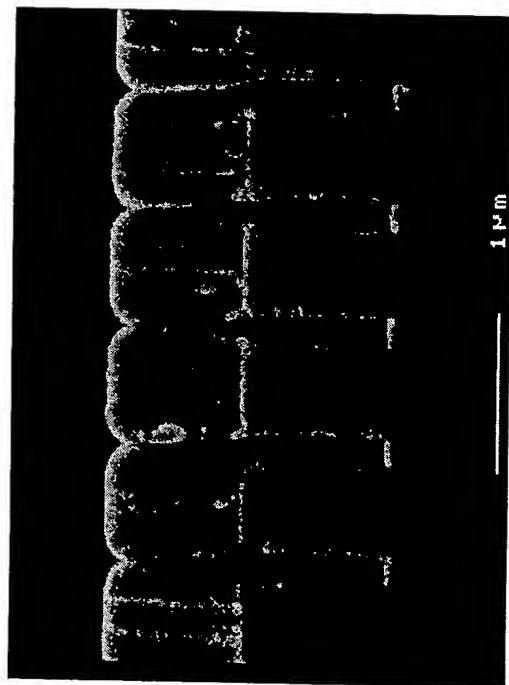
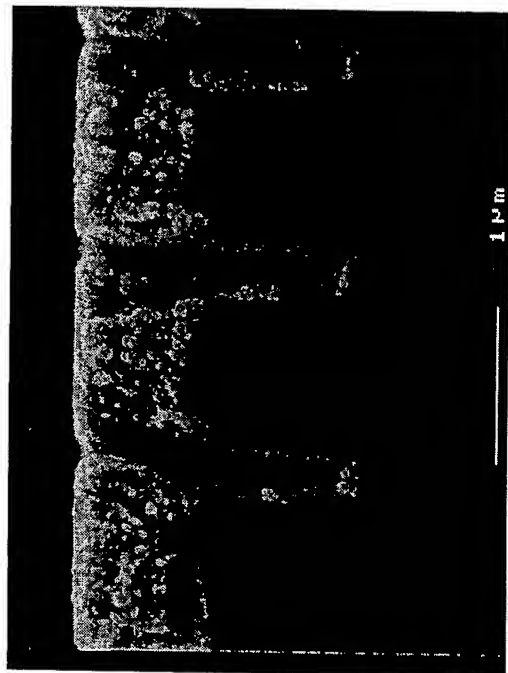
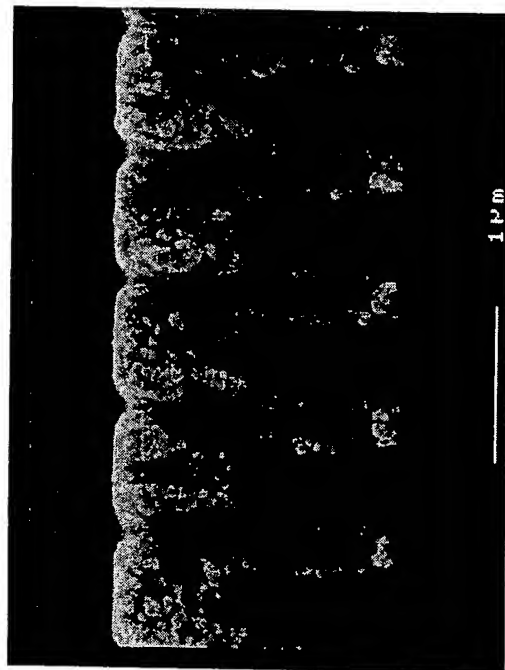


FIG 6B



Peak Surface Area Summit Zero Crossing Stopband Execute Cursor

Roughness Analysis

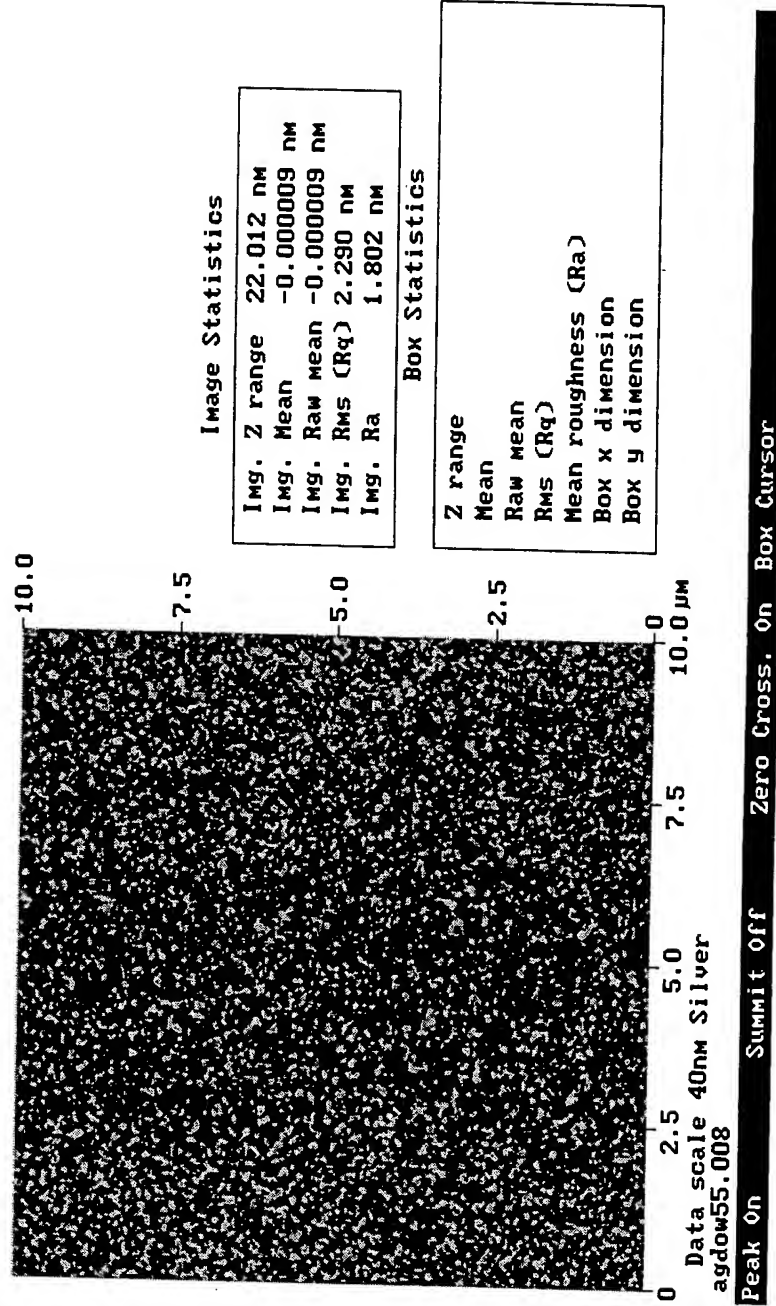


FIG 7A

Peak Surface Area Summit Zero Crossing Stopband Execute Cursor

Roughness Analysis

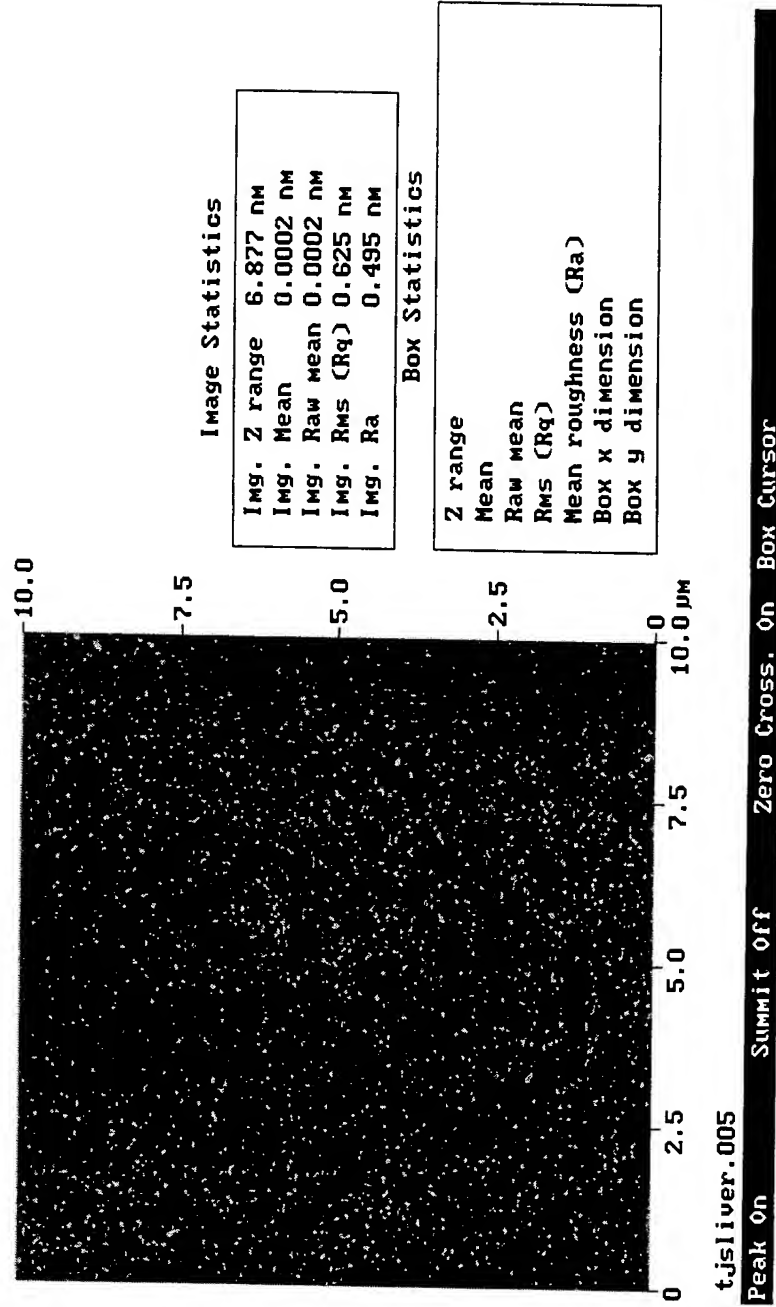


FIG 7B